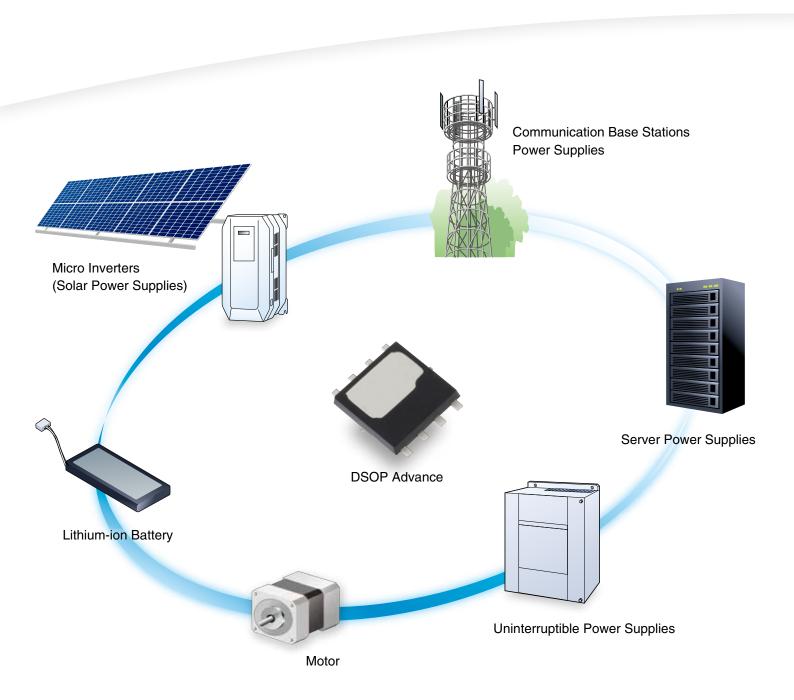


U-MOSIX/U-MOSVIII Series Low Voltage MOSFETs



Gen-9 and Gen-8 High-Performance U-MOS Series That Help Save Energy

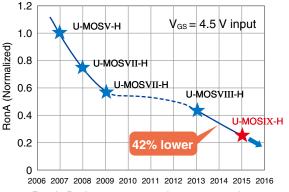
Low-Voss MOSFETs

Toshiba has used each successive generation of fabrication processes and steadily optimized the device structure to reduce the power losses of its low-voltage power MOSFETs.

Features

- Low on-resistance due to the use of a small-geometry process
- Low power losses due to a greatly improved trade-off between on-resistance and charge characteristics
- MOSFETs with a wide range of V_{DSS} and extensive packaging options suitable for various applications
- High avalanche ruggedness and ESD tolerance
- Device structure designed to reduce switching noise and thus simplify system design

[Continual Reduction in On-Resistance of 30-V MOSFETs]



RonA: Drain-source on-resistance per unit area

U-MOSIX and **U-MOSVIII** Series

The high-performance U-MOSIX and U-MOSVIII-H series combine low on-resistance and high switching speed and are available with a wide range of Voss from 30 V to 250 V.

[Comparison of Coverage of the U-MOSVIII-H and U-MOSIX-H Series]

Drain-Source	Drain-Source voltage Vpss (V)										
on-resistance R _{DS} (ON) (Max) @ V _{GS} = 10 V (mΩ)	30 V	40 V	45 V	60 V	75 V	80 V	100 V	120 V	150 V	200 V	250 V
100-200										1	11
50-100									11		1
20-50	FH			1		1	1			1	
10-20	± ↑ %	^		1			1	1	1		
5-10	1 XI ON	11						1			
3-5	U-MOSIX-H					1	1				
1–3	Ö		1	11 11	0		1				
0.7-1	1	1	1								
0.7 less than	1										

Double-Sided-Cooling Package DSOP Advance

1. The DSOP Advance package efficiently dissipates heat from the metal plates on the top and bottom surfaces.

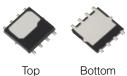
The DSOP Advance package provides a higher current capacity than the conventional package with the same size and therefore helps save PCB space and reduce the system size.

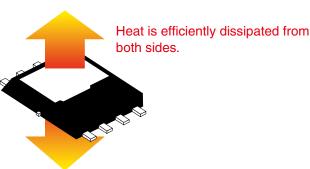
2. The DSOP Advance package is footprint-compatible with the SOP Advance package.

MOSFETs in the DSOP Advance package serve as easy replacements for those in the SOP Advance package without the need for modifying the PCB layout.

3. The DSOP Advance package has lower resistance.

[DSOP Advance Package]

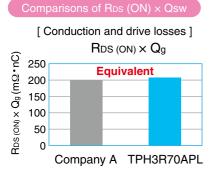


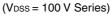


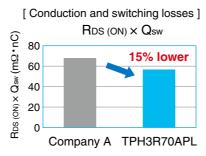
Features

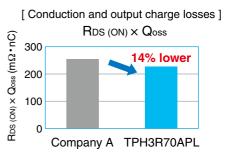
1. Greatly improved trade-off between on-resistance and charge characteristics

Fabricated with the latest process and the optimized cell structure, the U-MOSIX-H series provides a greatly improved trade-off between on-resistance and charge characteristics, which are important figures of merit for MOSFETs. Consequently, the U-MOSIX-H series provides significant reductions in major losses including conduction loss, drive loss, switching loss, and output charge loss, which help improve the efficiency of application systems and reduce the MOSFET device temperature.









As of January 2018 (as surveyed by Toshiba)

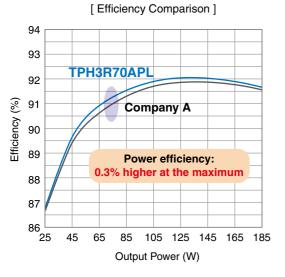
Rbs (on): Drain-source on-resistance (m Ω) (figure of merit for conduction loss) Qg: Gate charge (nC) (figure of merit for drive loss)

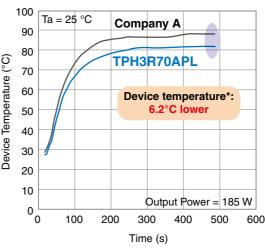
Qsw: Gate switch charge (nC) (figure of merit for switching loss)
Qoss: Output charge (nC) (figure of merit for output charge loss)

TPH3R70APL: U-MOSIX-H, SOP Advance VDSS = 100 V, RDS (ON) (Max) = 3.7 m Ω (VGS = 10 V input)

Comparisons of efficiency and device temperature

(Full-Bridge DC-DC Converter)





[Device Temperature Comparison]

Operating conditions:
Input voltage = 48 V
Output voltage = 24 V
Output power = 25 to 185 W
Operating frequency: 150 kHz
MOSFET gate drive voltage = 6 V

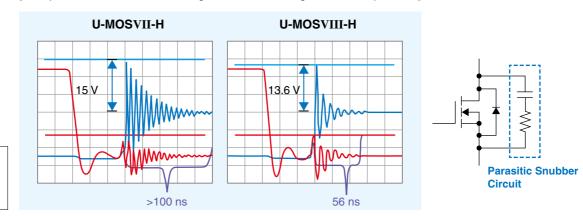
2. Reduction in switching noise

Test conditions: VIN = 12 V

Vout = 5 V lout = 12 A

Due to the parasitic RC snubber between drain and source, the U-MOSVIII-H and U-MOSIX-H series help reduce noise and ringing during switching transitions.

[Comparison of Drain-Source Voltage Waveforms during Switch-Off Operation]



3. Guaranteed at a channel temperature of up to 175°C

The MOSFETs of the U-MOSIX-H series, including those with a Vbss of 30 V, are guaranteed at a channel temperature of up to 175°C and over a storage temperature range from -55°C to 175°C.

^{*} At the center of the package mold surface

U-MOSIX/U-MOSVIII Series Lineup

VDSS	RDS (ON)	TSON Advance	SOP Advance	SOP-8	DSOP Advance	TO-220	TO-220SIS	DPAK	D2PAK	DPAK+	D2PAK+	TO-220SM (W)
(V)	max (mΩ)	•	•							•	•	•
	10 – 20	TPN11003NL	TPH11003NL									
	5 – 10	TPN8R903NL TPN6R303NC TPN6R003NL TPN5R203PL	TPH8R903NL TPH6R003NL	TP89R103NL TP86R303NL								
	3 – 5	TPN4R303NL TPN4R203NC	TPH4R803PL TPH4R003NL TPH3R203NL			TK3R3E03GL						
30	1 – 3	TPN2R903PL TPN2R703NL TPN2R503NC TPN2R203NC TPN1R603PL	TPH3R003PL TPH2R903PL TPH2R003PL TPH1R403NL									
	< 1		TPHR9203PL TPHR9003NL TPHR9003NC TPHR6503PL		TPWR8503NL TPWR6003PL							
	10 – 20									TK15S04N1L		
	5 – 10	TPN7R504PL	TPH7R204PL TPH6R004PL									
40	3 – 5	TPN3R704PL	TPH3R704PC TPH3R704PL			TK3R1E04PL	TK3R1A04PL	TK3R1P04PL		TK65S04N1L		
	1 – 3	TPN2R304PL	TPH2R104PL TPH1R204PB TPH1R204PL							TK100S04N1L TK1R4S04PB	TK1R5R04PB	TK1R4F04PB
	< 1		TPHR8504PL		TPWR8004PL							TK200F04N1L TKR74F04PB
45	1 – 3	TPN2R805PL	TPH2R805PL TPH1R405PL TPH1R005PL									
	< 1				TPW1R005PL							
	20 – 50	TPN22006NH										
60	10 – 20	TPN14006NH TPN11006NL TPN11006PL	TPH14006NH TPH11006NL			TK30E06N1 TK40E06N1	TK30A06N1 TK40A06N1			TK25S06N1L TK40S06N1L		
	5 – 10	TPN7R506NH TPN7R006PL	TPH9R506PL TPH7R506NH TPH7R006PL TPH5R906NH			TK8R2E06PL TK58E06N1 TK5R1E06PL	TK8R2A06PL TK58A06N1 TK5R3A06PL	TK6R7P06PL				
	3 – 5	TPN4R806PL	TPH4R606NH TPH3R506PL			TK4R3E06PL TK3R2E06PL	TK4R3A06PL TK3R3A06PL	TK4R4P06PL		TK90S06N1L		
	1 – 3		TPH2R306NH TPH2R506PL TPH1R306PL TPH1R306P1		TPW1R306PL	TK100E06N1	TK100A06N1					
75	1 – 3		TPH2R608NH		TPW2R508NH							
	30 – 50	TPN30008NH										
	10 – 20	TPN13008NH	TPH12008NH			TK35E08N1	TK35A08N1					
80	5 – 10		TPH8R008NH			TK46E08N1	TK46A08N1					
	3 – 5		TPH4R008NH		TPW4R008NH	TK72E08N1 TK100E08N1	TK72A08N1 TK100A08N1					

V _{DSS} (V)	R _{DS} (ON) max (mΩ)	TSON Advance	SOP Advance	SOP-8	DSOP Advance	TO-220	TO-220SIS	DPAK	D2PAK	DPAK+	D2PAK+	TO-220SM (W)
		•	•						•			
100	20 – 50	TPN3300ANH								TK11S10N1L TK7S10N1Z		
	10 – 20	TPN1600ANH TPN1200APL	TPH1400ANH			TK22E10N1 TK110E10PL	TK22A10N1 TK110A10PL	TK110P10PL				
	5 – 10		TPH8R80ANH TPH6R30ANL TPH5R60APL			TK34E10N1 TK40E10N1 TK7R2E10PL TK6R4E10PL	TK34A10N1 TK40A10N1 TK7R4A10PL TK6R7A10PL	TK7R7P10PL		TK33S10N1L TK33S10N1Z TK60S10N1L	TK60R10N1L	TK60F10N1L
	3 – 5		TPH4R50ANH TPH4R10ANL TPH3R70APL		TPW4R50ANH TPW3R70APL	TK65E10N1 TK3R9E10PL TK100E10N1	TK65A10N1 TK4R1A10PL TK100A10N1 TK3R2A10PL		TK65G10N1			TK160F10N1L TK160F10N1
	1 – 3					TK2R9E10PL						
	10 – 20					TK32E12N1	TK32A12N1					
120	5 – 10					TK42E12N1 TK56E12N1	TK42A12N1 TK56A12N1					
	3 – 5					TK72E12N1	TK72A12N1					
150	50 – 100	TPN5900CNH	TPH5900CNH									
	20 – 50		TPH3300CNH									
	10 – 20		TPH1500CNH		TPW1500CNH							
200	100 – 200	TPN1110ENH	TPH1110ENH									
	50 – 100		TPH6400ENH									
	20 – 50		TPH2900ENH		TPW2900ENH							
	200 – 300	TPN2010FNH	TPH2010FNH									
250	100 – 200		TPH1110FNH									
	50 – 100		TPH5200FNH		TPW5200FNH							

Part Naming Conventions

High-pin-count series

TPH 4R6 0 6 N H Additional information Product series N: U-MOSVIII/U-MOSVIII-H P: U-MOSIX/U-MOSIX-H Maximum rated voltage - Polarity / internal connection On-resistance (maximum rating under the maximum guaranteed drive conditions) R46: RDS (ON) = 0.46 mΩ 4R6: RDS (ON) = 4.6 mΩ 100: RDS (ON) = 10 mΩ (= 10 x 10°) 101: RDS (ON) = 100 mΩ (= 10 x 10°) Package symbol

MOSFETs in a conventional 3-pin package

- Current rating

Polarity

TK 11 S 10 N 1 L Additional information Additional information - Product series N: U-MOSVIII/U-MOSVIII-H P: U-MOSIX/U-MOSIX-H — Maximum rated voltage VDSS x 10% Package symbol

MOSFETs in a new 3-pin package

TK R74 F 04 P B

- Product series P: U-MOSIX/U-MOSIX-H - Maximum rated voltage VDSS x 10% Package symbol MOSFET with a V_{DSS} lower than 400 V

Additional information

R74: RDS (ON) = $0.74 \text{ m}\Omega$

7R4: Rbs (oN) = 7.4 m Ω 7R4: Rbs (oN) = 7.4 m Ω 740: Rbs (oN) = 74 m Ω (= 74 x 10°) 741: Rbs (oN) = 740 m Ω (= 74 x 10¹)

Polarity

Mar. 2018

BCE0118B

Low Voltage MOSFETs U-MOSIX/U-MOSVIII Series

U-MOSIX/U-MOSVIII Series Low Voltage MOSFETs

RESTRICTIONS ON PRODUCT USE

Toshiba Corporation and its subsidiaries and affiliates are collectively referred to as "TOSHIBA". Hardware, software and systems described in this document are collectively referred to as "Product"

- ▶ TOSHIBA reserves the right to make changes to the information in this document and related Product without notice.
- This document and any information herein may not be reproduced without prior written permission from TOSHIBA. Even with TOSHIBA's written permission, reproduction is permissible only if reproduction is without alteration/omission.
- Though TOSHIBA works continually to improve Product's quality and reliability, Product can malfunction or fail. Customers are responsible for complying with safety standards and for providing adequate designs and safeguards for their hardware, software and systems which minimize risk and avoid situations in which a malfunction or failure of Product could cause loss of human life, bodily injury or damage to property, including data loss or corruption. Before customers use the Product, create designs including the Product, or incorporate the Product into their own applications, customers must also refer to and comply with (a) the latest versions of all relevant TOSHIBA information, including without limitation, this document, the specifications, the data sheets and application notes for Product and the precautions and conditions set forth in the "TOSHIBA Semiconductor Reliability Handbook" and (b) the instructions for the application with which the Product will be used with or for. Customers are solely responsible for all aspects of their own product design or applications, including but not limited to (a) determining the appropriateness of the use of this Product in such design or applications; (b) evaluating and determining the applicability of any information contained in this document, or in charts, diagrams, programs, algorithms, sample application circuits, or any other referenced documents; and (c) validating all operating parameters for such designs and applications. TOSHIBA ASSUMES NO LIABILITY FOR CUSTOMERS' PRODUCT DESIGN OR APPLICATIONS.
- PRODUCT IS NEITHER INTENDED NOR WARRANTED FOR USE IN EQUIPMENTS OR SYSTEMS THAT REQUIRE EXTRAORDINARILY HIGH LEVELS OF QUALITY AND/OR RELIABILITY, AND/OR A MALFUNCTION OR FAILURE OF WHICH MAY CAUSE LOSS OF HUMAN LIFE, BODILY INJURY, SERIOUS PROPERTY DAMAGE AND/OR SERIOUS PUBLIC IMPACT ("UNINTENDED USE"). Except for specific applications as expressly stated in this document, Unintended Use includes, without limitation, equipment used in nuclear facilities, equipment used in rautomobiles, trains, ships and other transportation, traffic signalling equipment, equipment used to control combustions or explosions, safety devices, elevators and escalators, devices related to electric power, and equipment used in finance-related fields. IF YOU USE PRODUCT FOR UNINTENDED USE, TOSHIBA ASSUMES NO LIABILITY FOR PRODUCT. For details, please contact your TOSHIBA sales representative.
- Do not disassemble, analyze, reverse-engineer, alter, modify, translate or copy Product, whether in whole or in part.
- Product shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable laws or regulations.
- ► The information contained herein is presented only as guidance for Product use. No responsibility is assumed by TOSHIBA for any infringement of patents or any other intellectual property rights of third parties that may result from the use of Product. No license to any intellectual property right is granted by this document, whether express or implied, by estoppel or otherwise.
- ABSENT A WRITTEN SIGNED AGREEMENT, EXCEPT AS PROVIDED IN THE RELEVANT TERMS AND CONDITIONS OF SALE FOR PRODUCT, AND TO THE MAXIMUM EXTENT ALLOWABLE BY LAW, TOSHIBA (1) ASSUMES NO LIABILITY WHATSOEVER, INCLUDING WITHOUT LIMITATION, INDIRECT, CONSEQUENTIAL, SPECIAL, OR INCIDENTAL DAMAGES OR LOSS, INCLUDING WITHOUT LIMITATION, LOSS OF PROFITS, LOSS OF OPPORTUNITIES, BUSINESS INTERRUPTION AND LOSS OF DATA, AND (2) DISCLAIMS ANY, AND ALL EXPRESS OR IMPLIED WARRANTIES AND CONDITIONS RELATED TO SALE, USE OF PRODUCT, OR INFORMATION, INCLUDING WARRANTIES OR CONDITIONS OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, ACCURACY OF INFORMATION, OR NONINFRINGEMENT
- ▶ Do not use or otherwise make available Product or related software or technology for any military purposes, including without limitation, for the design, development, use, stockpiling or manufacturing of nuclear, chemical, or biological weapons or missile technology products (mass destruction weapons). Product and related software and technology may be controlled under the applicable export laws and regulations including, without limitation, the Japanese Foreign Exchange and Foreign Trade Law and the U.S. Export Administration Regulations. Export and re-export of Product or related software or technology are strictly prohibited except in compliance with all applicable export laws and regulations.
- ▶ Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. Please use Product in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. TOSHIBA ASSUMES NO LIABILITY FOR DAMAGES OR LOSSES OCCURRING AS A RESULT OF NONCOMPLIANCE WITH APPLICABLE LAWS AND REGULATIONS.

TOSHIBA

TOSHIBA ELECTRONIC DEVICES & STORAGE CORPORATION

Website: https://toshiba.semicon-storage.com/